

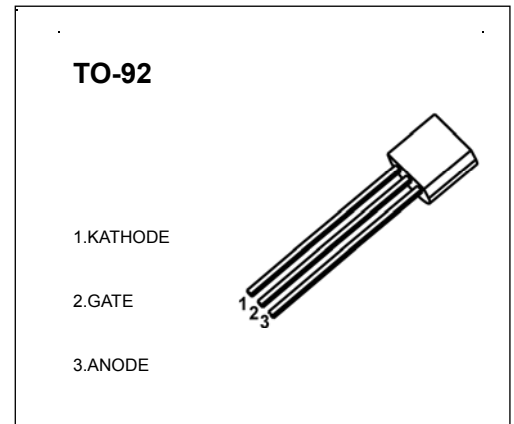


**TO-92 Plastic-Encapsulate Thyristors**

**MCR 100- 6,- 8 Silicon Planar PNP Thyristor**

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
$V_{DRM}$	MCR100-6	400
	MCR100-8	600
$T_j$	Junction Temperature	-40 ~ 125 °C
$T_{stg}$	Storage Temperature	-55 ~ 150 °C



**DESCRIPTION**

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

**FEATURES**

- Blocking voltage to 400 V (MCR100-6)
- RMS on-state current to 0.8 A
- General purpose switching

**APPLICATIONS**

- General purpose switching
- Phase control applications
- Solid state relays

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage *	$V_{TM}$	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	$V_{GT}$	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward blocking voltage	$V_{DRM}$	$I_{DRM}= 10 \mu A$	400		V	
MCR100-6 MCR100-8			600			
Peak forward or reverse blocking Current	$I_{DRM}$ $I_{RRM}$	$V_{AK}= \text{Rated}$ $V_{DRM}$ or $V_{RRM}$		10	$\mu A$	
Holding current	$I_H$	$I_{HL}=20mA, V_{AK}=7V$		5	mA	
Gate trigger current	$I_{GT}$	$V_{AK}=7V$	A2	5	15	$\mu A$
			A1	15	30	$\mu A$
			A	30	80	$\mu A$
			B	80	200	$\mu A$

\* Forward current applied for 1 ms maximum duration, duty cycle ≤ 1%.